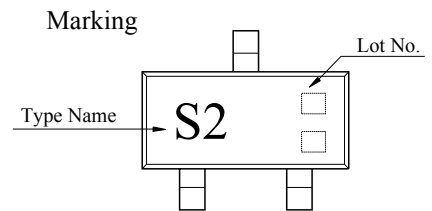
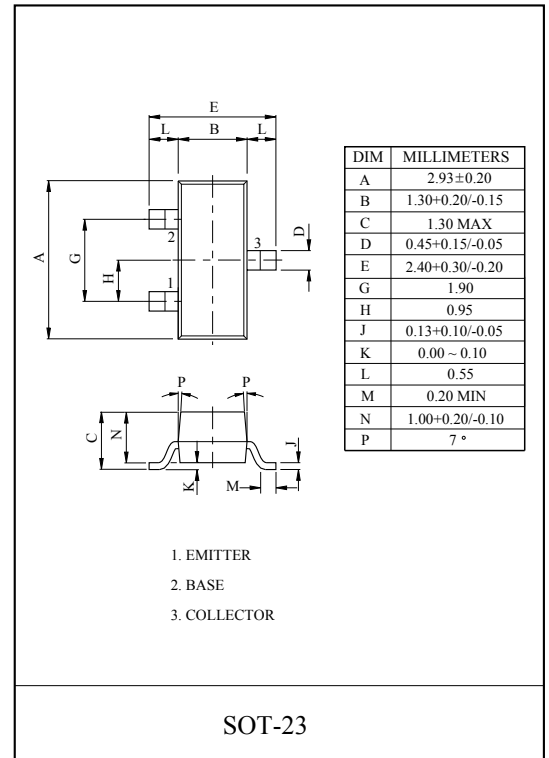


HIGH FREQUENCY APPLICATION.
VHF BAND AMPLIFIER APPLICATION.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	100	mA
Emitter Current	I_E	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-65 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=3mA, I_B=0$	15	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1\mu A, I_E=0$	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	3.0	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=15V, I_E=0$	-	-	10	nA
DC Current Gain	h_{FE}	$V_{CE}=1V, I_C=3mA$	20	-	-	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	1.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	0.4	V
Transition Frequency	f_T	$I_C=4mA, V_{CE}=10V, f=100MHz$	600	-	-	MHz
Collector Input Capacitance	C_{ib}	$V_{EB}=0.5V, I_C=0, f=1MHz$	-	-	2.0	pF
Collector Output Capacitance	C_{ob}	$V_{CB}=0V, I_E=0, f=1MHz$	-	-	3.0	pF
		$V_{CB}=10V, I_E=0, f=1MHz$	-	-	1.7	
Noise Figure	NF	$V_{CE}=6V, I_C=1mA,$ $R_g=400\Omega, f=60MHz$	-	-	6.0	dB